EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	2002/0130390	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/10 15:01
S2	2	"6,667,870"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 12:06
S3	2	("5239440" | "6104588").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/16 11:43
S4	4605	(MOS MOSFET FET field near effect) same gate near capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 12:11
S5	119	(MOS MOSFET FET field near effect) same gate near channel near capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 12:26
S6	12	esd and NMOS near capacitor and PMOS near capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:11
S7	15	(esd electrostatic) and NMOS near capacitor and PMOS near capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 12:28
S8	8	("5034845" | "5301084" | "5654862" | "5907464" | "5946177" | "5956219" | "6385021" | "6724603").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/16 12:52
S9	4	esd and NMOS near capacitor and PMOS near resistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:11

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S10	51	"5,287,241"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 13:32
S11	1	10/508,879	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 13:32
S12	314	PMOS near capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:11
S13	26	esd and NMOS near3 capacitor and PMOS near3 resistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:13
S14	18	esd and NMOS near3 capacitor and PMOS near3 resistor and PMOS near3 capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:27
S15	0	esd and PMOS near3 capacitor same (substrate bulk) near power same (drain source) near ground	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:29
S16	0	esd and PMOS near3 capacitor and (substrate bulk) near power same (drain source) near ground	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:30
S17	0	esd and PMOS near3 capacitor same (substrate bulk) near power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:31

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S18	0	PMOS near3 capacitor same (substrate bulk) near power	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:32
S19	0	MOSFET near3 capacitor near non adj linear near characteristic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:45
S20	88152	MOSFET gate near capacit$3 near non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:46
S21	0	MOSFET near gate near capacit$3 near non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:46
S22	2	MOSFET near gate near capacit$3 near5 non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:48
S23	2	MOSFET near gate near capacit$3 near9 non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:53
S24	2	MOSFET near gate near capacit$3 same non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:48
S25	6	("5410273").URPN.	USPAT	OR	ON	2006/02/16 14:49
S26	2	(MOSFET FET field adj effect) near gate near capacit$3 near9 non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:54

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S27	2	(MOSFET FET field adj effect) near3 gate near capacit$3 near9 non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 14:55
S28	5	(MOSFET FET field adj effect) near3 gate near capacit$3 same non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 16:12
S29	6	(MOSFET FET field adj effect) near5 gate near capacit$3 same non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 16:13
S30	16	(MOSFET FET field adj effect) near3 gate near capacit$4 same non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 16:27
S31	28	(MOSFET FET field adj effect) near5 gate near capacit$4 same non near linear	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 16:51
S32	1764	361/111.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 16:52
S33	1	esd and PMOS with (substrate bulk) with power with gate with node with (source drain) with ground	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 11:52
S34	2	("5838050" | "6166584").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/17 11:51
S35	4	PMOS with capacit$3 with (substrate bulk) with power with gate with node with (source drain) with ground	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 12:04

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S36	3	"6,912,109"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 12:04
S37	11	("4855620" | "5086365" | "5237395" | "5255146" | "5287241" | "5311391" | "5440162" | "5610791" | "5625280" | "5631793" | "6008970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/02/17 14:57
S38	1	10/508,879	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 15:06
S39	580	gate near capacit$4 same breakdown	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 15:06
S40	268	gate near capacit$4 with breakdown	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 15:06
S41	9	esd and gate near capacit$4 with breakdown	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 15:14
S42	13	esd and gate near capacit$4 with threshold	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 15:14
S43	631	361/91.1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/17 16:36

S44	1183	361/91.5.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/19 12:01
S45	1	10/508,879	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/08 15:45
S46	4	"6,912,109"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/08 15:46
S47	11	("4855620" | "5086365" | "5237395" | "5255146" | "5287241" | "5311391" | "5440162" | "5610791" | "5625280" | "5631793" | "6008970").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/08 15:46
S48	2559	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/08 15:56
S49	41	("5222146"|"5239440"|"5323067"|"5440162"|"5508649"|"5744842"|"5907464"|"5978192"|"6016070"|"6198138"|"6385021"|"6392860"|"6400540"|"6510033"|"6566715"|"6643109"|"6664823"|"6795286"|"6903913"|"6927957").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/08 16:17
S50	2559	361/56.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/08 16:35
S51	1799	361/111.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/10 10:25

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S52	670	361/91.1.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/10 11:40
S53	1187	361/91.5.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/10 12:52
S54	1187	361/91.5.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/10 15:01
S55	25	esd and ((MOSFET FET MOS field adj effect) same capacitor same gate same source same drain).clm.	US-PGPUB	OR	ON	2006/09/10 15:13